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(54) Title: IMPROVED FORMULATIONS FOR HIGH SELECTIVE SILICON NITRIDE ETCH

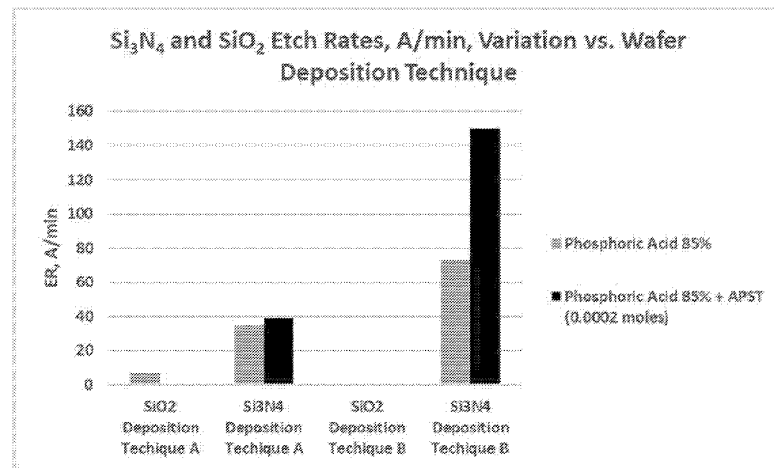


FIGURE 1

(57) Abstract: Compositions useful for the selective removal of silicon nitride materials relative to polysilicon, silicon oxide materials and/or silicide materials from a microelectronic device having same thereon are provided. The compositions of the invention are particularly useful in the etching of 3D NAND structures.

[Continued on next page]

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